

TLV742P 200mA 小尺寸低压降线性稳压器

1 特性

- 输入电压范围：2V 至 5.5V
- 可提供 0.85V 至 5V 范围（以 50mV 为增量）内的固定输出电压组合⁽¹⁾
- 典型精度为 0.5%
- 高 PSRR：
 - 1MHz 时为 55dB
- 启用时的 I_Q ：25 μ A
- 禁用时的 I_Q ：1 μ A
- 有源输出放电
- 热关断保护和过流保护
- 封装：
 - 1mm × 1mm DQN (X2SON)

2 应用

- 销售终端
- 摄像头和机器视觉模块
- 游戏和玩具
- 楼宇自动化和视频监控
- 电视和机顶盒

3 说明

TLV742P 系列低压降线性稳压器 (LDO) 经过优化，能够通过支持宽输出电压范围提供出色的性能。这些 LDO 可将单节锂离子电池的输入至输出电压直接调节为低至 0.85V。如果此器件用于对直流/直流转换器输出进行后期调节，则其在 1MHz 下的 55dB 高 PSRR 可抑制纹波，从而提供低噪声且良好调节的稳定 V_{OUT} 。

TLV742P 具备有源输出放电特性，有助于在系统处于禁用状态、待机模式或睡眠模式时确保输出保持低电平。此外，该器件的过流保护功能可在输出短路的情况下保护器件，并且其热关断功能可防止过热。

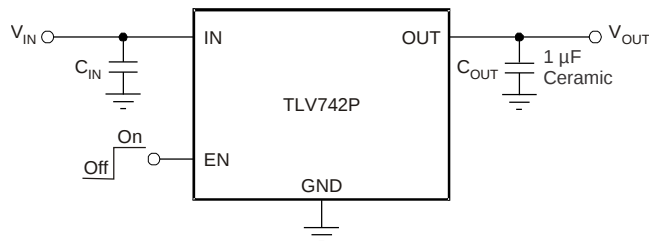
TLV742P 系列稳压器采用 1mm × 1mm X2SON 封装，因此可最大限度减少 PCB 面积。

器件信息⁽¹⁾

器件型号	封装	封装尺寸（标称值）
TLV742P	X2SON (4)	1.00mm x 1.00mm

(1) 如需了解所有可用封装，请参阅产品说明书末尾的可订购产品附录。

典型应用电路



Copyright © 2017, Texas Instruments Incorporated



目录

1	特性	1	8	Application and Implementation	15
2	应用	1	8.1	Application Information.....	15
3	说明	1	8.2	Typical Application	15
4	修订历史记录	2	8.3	Do's and Don'ts.....	18
5	Pin Configuration and Functions	3	9	Power Supply Recommendations	19
6	Specifications	4	10	Layout	19
6.1	Absolute Maximum Ratings	4	10.1	Layout Guidelines	19
6.2	ESD Ratings.....	4	10.2	Layout Example	20
6.3	Recommended Operating Conditions.....	4	10.3	Thermal Considerations	20
6.4	Thermal Information	4	10.4	Power Dissipation	20
6.5	Electrical Characteristics.....	5	11	器件和文档支持	21
6.6	Typical Characteristics	6	11.1	器件支持	21
7	Detailed Description	13	11.2	接收文档更新通知	21
7.1	Overview	13	11.3	社区资源	21
7.2	Functional Block Diagrams	13	11.4	商标	21
7.3	Feature Description.....	13	11.5	静电放电警告	21
7.4	Device Functional Modes.....	14	11.6	Glossary	21
			12	机械、封装和可订购信息	22

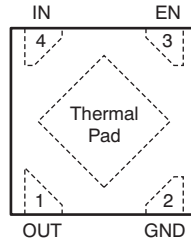
4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

日期	修订版本	说明
2017 年 9 月	*	初始发行版。

5 Pin Configuration and Functions

DQN Package
4-Pin X2SON With Exposed Thermal Pad
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
EN	3	I	Enable pin. Driving EN over 0.9 V turns on the regulator. Driving EN below 0.4 V puts the regulator into shutdown mode. For TLV742P, output voltage is discharged through an internal 120-Ω resistor when device is shut down.
GND	2	—	Ground pin
IN	4	I	Input pin. For good transient performance, place a small 1-μF ceramic capacitor from this pin to ground. See Input and Output Capacitor Requirements for more details.
OUT	1	O	Regulated output voltage pin. A small 1-μF ceramic capacitor is required from this pin to ground to ensure stability. See Input and Output Capacitor Requirements for more details.
Thermal pad	—	—	The thermal pad is electrically connected to the GND node. Connect to the GND plane for improved thermal performance.

6 Specifications

6.1 Absolute Maximum Ratings

over operating junction temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Voltage ⁽²⁾	IN	−0.3	6	V
	EN	−0.3	6	V
	OUT	−0.3	6	V
Current (source)	OUT	Internally limited		
Output short-circuit duration		Indefinite		
Operating junction, T _J		−55	150	°C
Storage, T _{stg}		−55	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to GND pin.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD) Electrostatic discharge	Human body model (HBM) QSS 009-105 (JESD22-A114A) ⁽¹⁾	±2000	V
	Charged device model (CDM) QSS 009-147 (JESD22-C101B.01) ⁽²⁾	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{IN}	Input voltage	2		5.5	V
I _{OUT}	Output current	0		200	mA
T _J	Operating junction temperature range	−40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TLV742P	UNIT
		DQN (X2SON)	
		4 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	180.4	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	152	°C/W
R _{θJB}	Junction-to-board thermal resistance	117.2	°C/W
ψ _{JT}	Junction-to-top characterization parameter	5.1	°C/W
ψ _{JB}	Junction-to-board characterization parameter	117	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	99.7	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

at $V_{IN} = V_{OUT(NOM)} + 0.5 \text{ V}$ or 2 V (whichever is greater); $I_{OUT} = 1 \text{ mA}$, $V_{EN} = V_{IN}$, $C_{OUT} = 0.47 \mu\text{F}$, and $T_J = -40^\circ\text{C}$ to $+85^\circ\text{C}$. Typical values are at $T_J = 25^\circ\text{C}$, (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP	MAX	UNIT
V _{IN}	Input voltage range				2		5.5	V
V _{OUT}	Output voltage range				0.85		5	V
	DC output accuracy				0.5%			
		V _{OUT} ≥ 0.85 V			−1.5%		1.5%	
ΔV _{O(ΔVI)}	Line regulation					1	5	mV
ΔV _{O(ΔIO)}	Load regulation	0 mA ≤ I _{OUT} ≤ 150 mA				10	20	mV
V _(DO)	Dropout voltage	V _{IN} = 0.98 × V _{OUT(NOM)}	2 V < V _{OUT} ≤ 2.4 V	I _{OUT} = 30 mA		65		mV
				I _{OUT} = 150 mA		325	360	mV
			2.4 V < V _{OUT} ≤ 2.8 V	I _{OUT} = 30 mA		50		mV
				I _{OUT} = 150 mA		250	300	mV
			2.8 V < V _{OUT} ≤ 3.3 V	I _{OUT} = 30 mA		45		mV
				I _{OUT} = 150 mA		220	270	mV
			3.3 V < V _{OUT} ≤ 5 V	I _{OUT} = 30 mA		40		mV
				I _{OUT} = 150 mA		200	250	mV
I _{CL}	Output current limit	V _{OUT} = 0.9 × V _{OUT(NOM)}			240	300	450	mA
I _(GND)	Ground pin current	I _{OUT} = 0 mA				25	50	μA
I _(EN)	EN pin current	V _{EN} = 5.5 V				0.01		μA
I _{SHUTDOWN}	Shutdown current	V _{EN} ≤ 0.4 V 2 V ≤ V _{IN} ≤ 4.5 V				1		μA
V _{IL(EN)}	EN pin low-level input voltage (disable device)				0		0.4	V
V _{IH(EN)}	EN pin high-level input voltage (enable device)				0.9		V _{IN}	V
PSRR	Power-supply rejection ratio	V _{IN} = 3.3 V V _{OUT} = 2.8 V I _{OUT} = 30 mA	f = 100 Hz		70		dB	
			f = 10 kHz		55			
			f = 1 MHz		55			
V _n	Output noise voltage	BW = 100 Hz to 100 kHz, V _{IN} = 2.3 V V _{OUT} = 1.8 V I _{OUT} = 10 mA				45		μV _{RMS}
t _{STR}	Startup time ⁽¹⁾	C _{OUT} = 1 μF I _{OUT} = 150 mA				100		μs
R _{PULLDOWN}	Pulldown resistance (TLV742P only)					120		Ω
T _J	Operating junction temperature				−40		125	°C

(1) Start-up time = time from EN assertion to $0.98 \times V_{OUT}$.

6.6 Typical Characteristics

at $T_J = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ or 2 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, and $C_{OUT} = 1\text{ }\mu\text{F}$
 Typical values are at $T_J = 25^{\circ}\text{C}$, (unless otherwise noted)

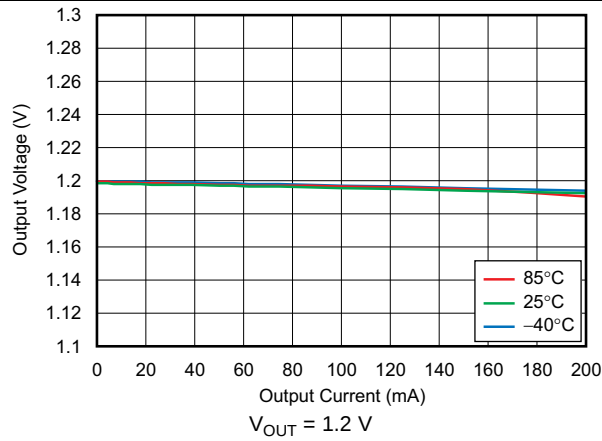


图 1. Load Regulation

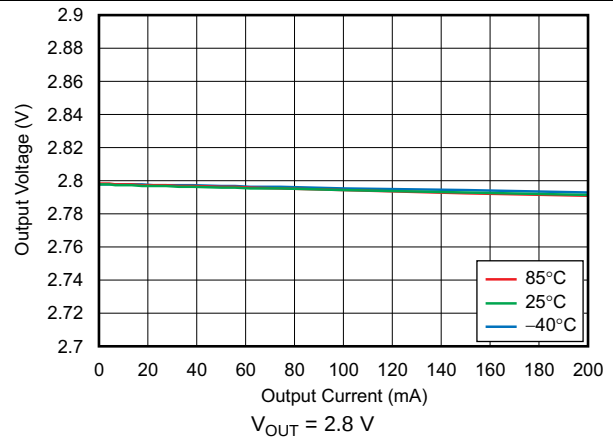


图 2. Load Regulation

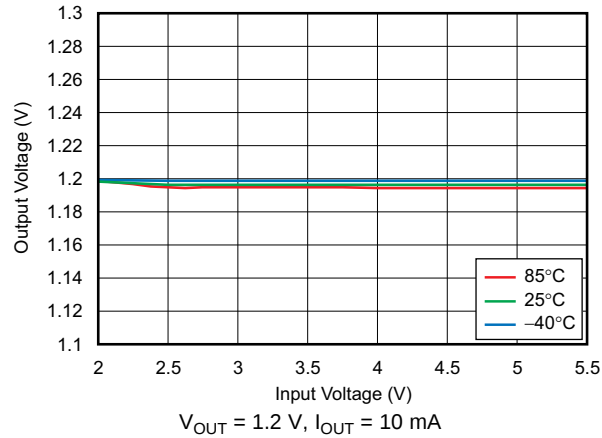


图 3. Line Regulation

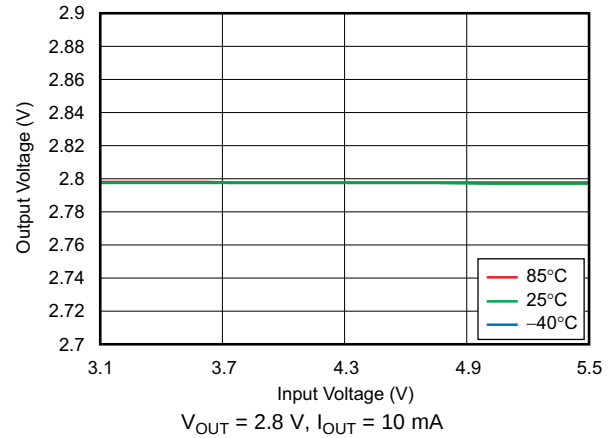


图 4. Line Regulation

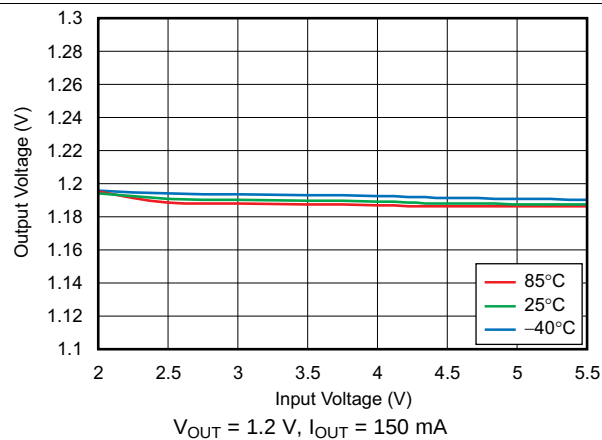


图 5. Line Regulation

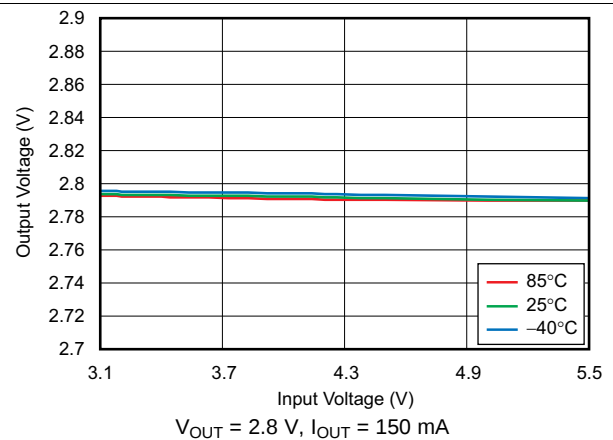


图 6. Line Regulation

Typical Characteristics (接下页)

at $T_J = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ or 2 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, and $C_{OUT} = 1\text{ }\mu\text{F}$
Typical values are at $T_J = 25^{\circ}\text{C}$, (unless otherwise noted)

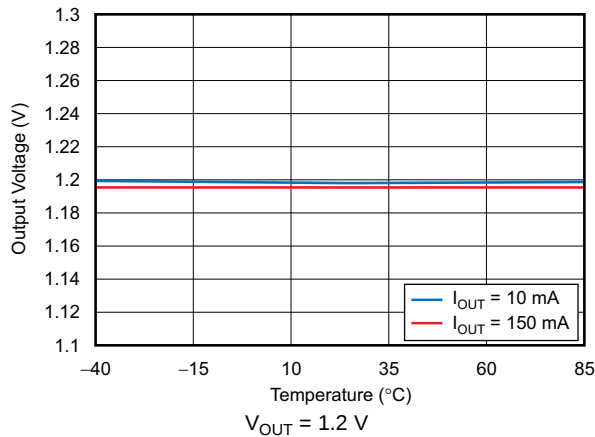


图 7. Output Voltage vs Temperature

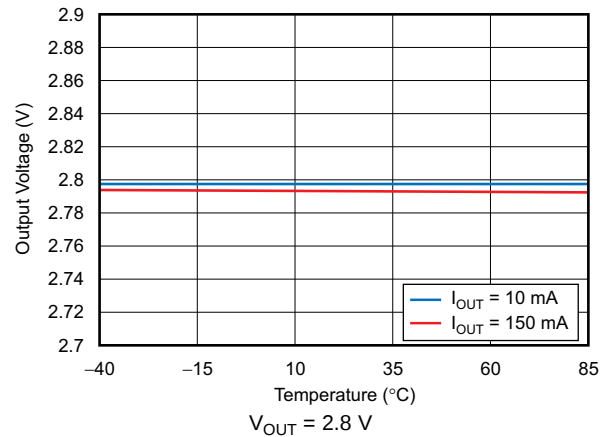


图 8. Output Voltage vs Temperature

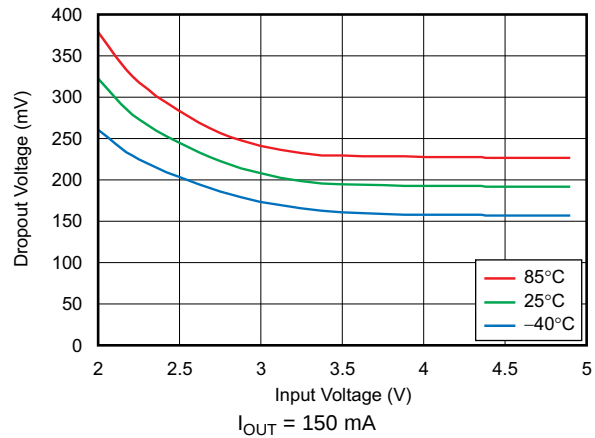


图 9. Dropout Voltage vs Input Voltage

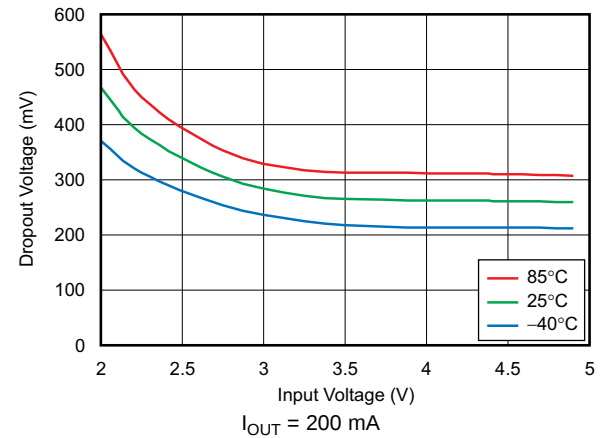


图 10. Dropout Voltage vs Input Voltage

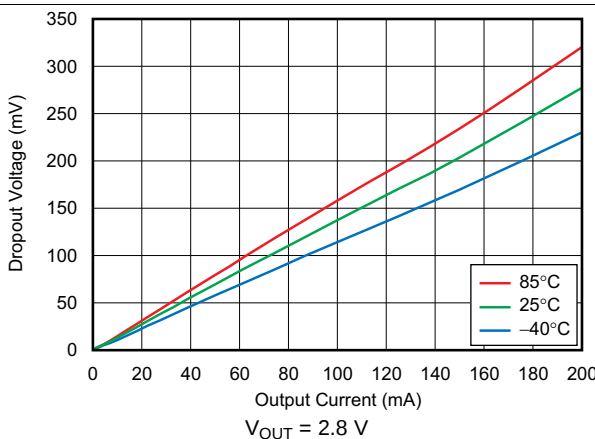


图 11. Dropout Voltage vs Output Current

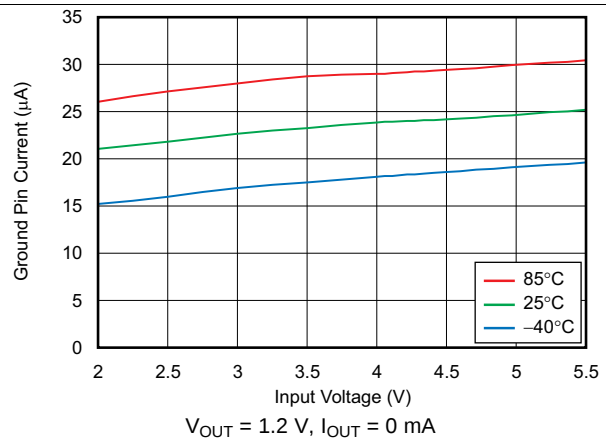


图 12. Ground Pin Current vs Input Voltage

Typical Characteristics (接下页)

at $T_J = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ or 2 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, and $C_{OUT} = 1\text{ }\mu\text{F}$
 Typical values are at $T_J = 25^{\circ}\text{C}$, (unless otherwise noted)

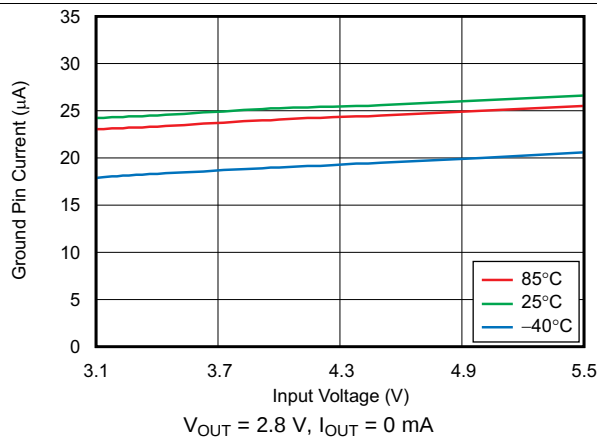


图 13. Ground Pin Current vs Input Voltage

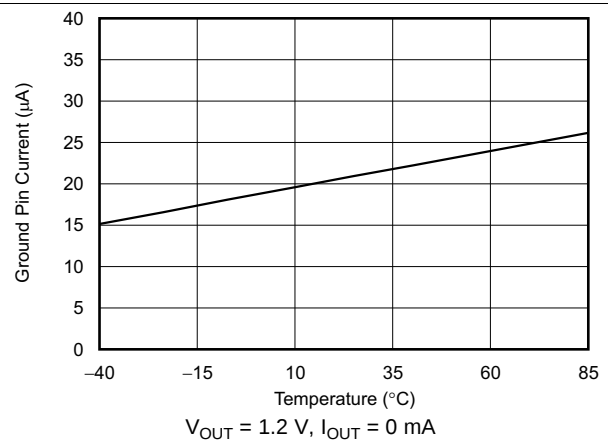


图 14. Ground Pin Current vs Temperature

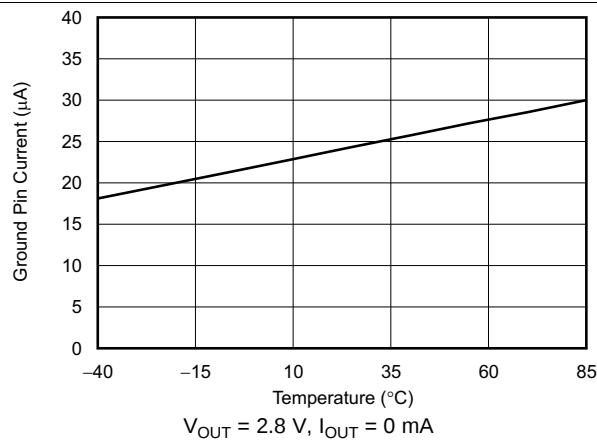


图 15. Ground Pin Current vs Temperature

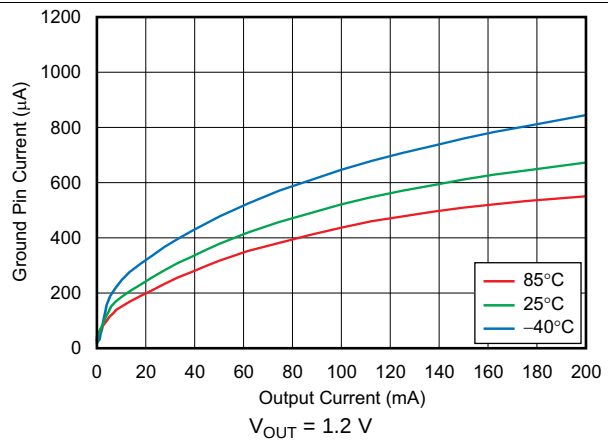


图 16. Ground Pin Current vs Output Current

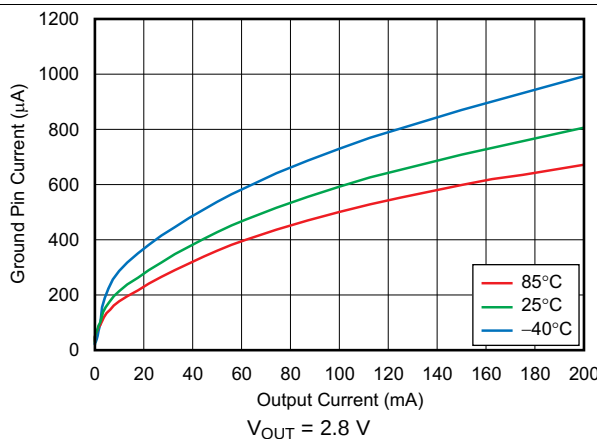


图 17. Ground Pin Current vs Output Current

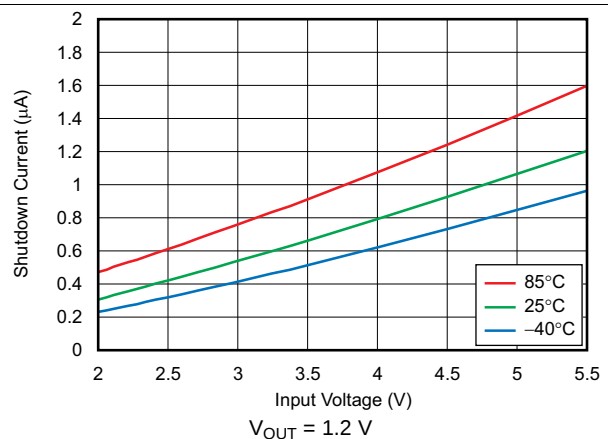


图 18. Shutdown Current vs Input Voltage

Typical Characteristics (接下页)

at $T_J = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ or 2 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, and $C_{OUT} = 1\text{ }\mu\text{F}$
Typical values are at $T_J = 25^{\circ}\text{C}$, (unless otherwise noted)

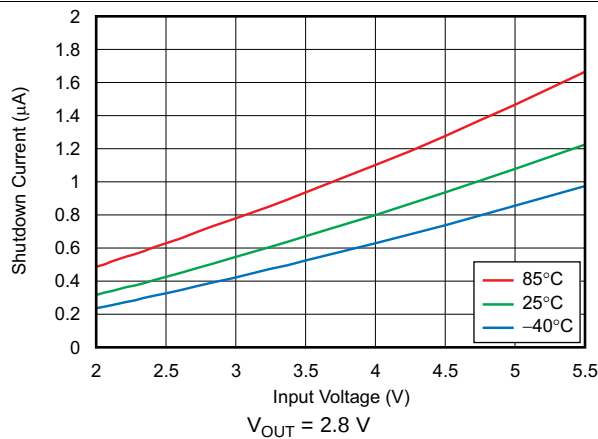


图 19. Shutdown Current vs Input Voltage

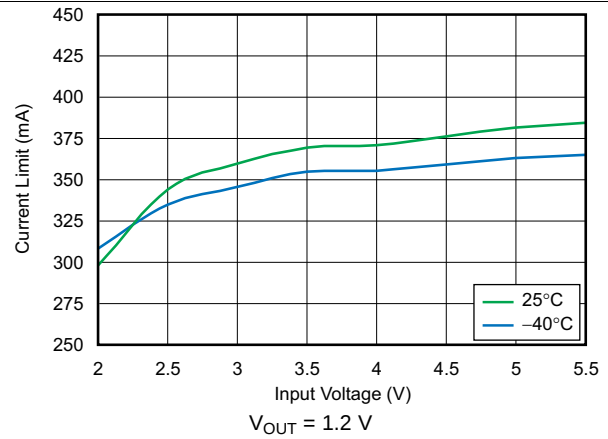


图 20. Current Limit vs Input Voltage

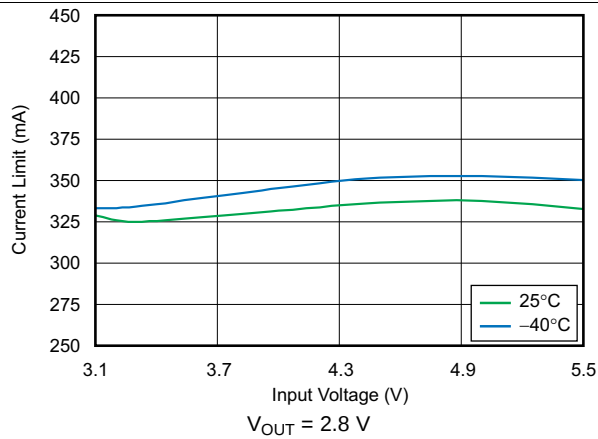


图 21. Current Limit vs Input Voltage

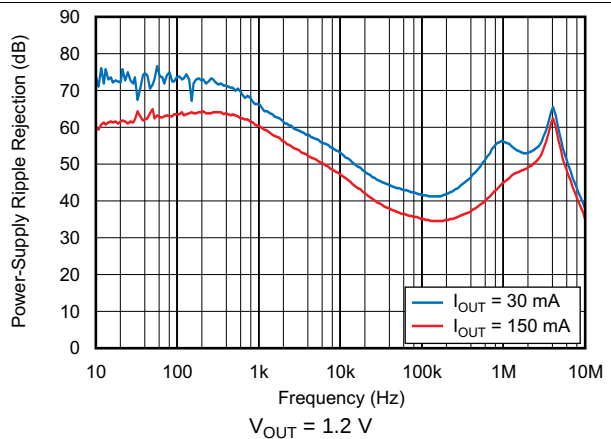


图 22. Power-Supply Ripple Rejection vs Frequency

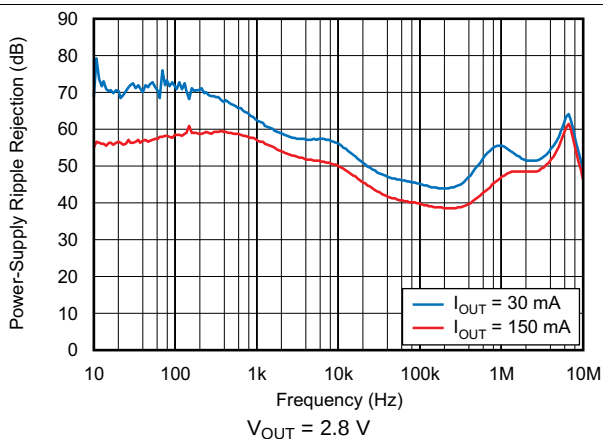


图 23. Power-Supply Ripple Rejection vs Frequency

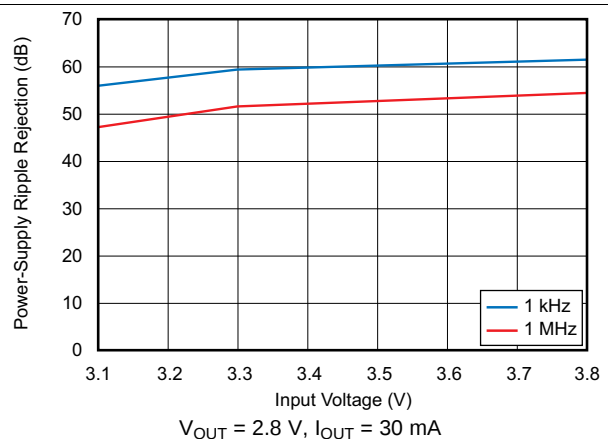


图 24. Power-Supply Ripple Rejection vs Input Voltage

Typical Characteristics (接下页)

at $T_J = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ or 2 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, and $C_{OUT} = 1\text{ }\mu\text{F}$
 Typical values are at $T_J = 25^{\circ}\text{C}$, (unless otherwise noted)

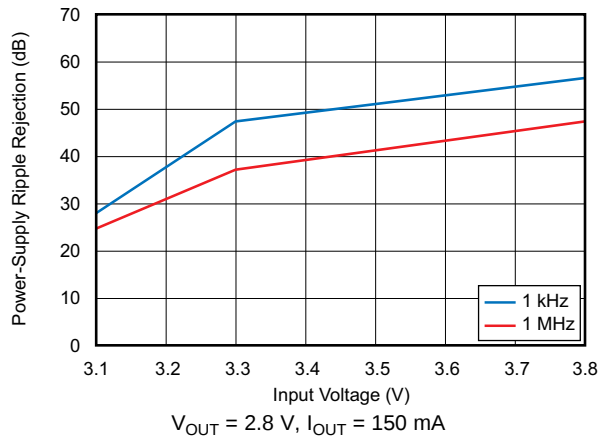


图 25. Power-Supply Ripple Rejection vs Input Voltage

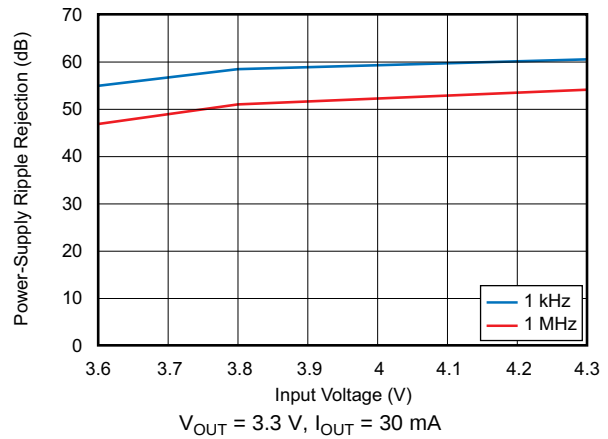


图 26. Power-Supply Ripple Rejection vs Input Voltage

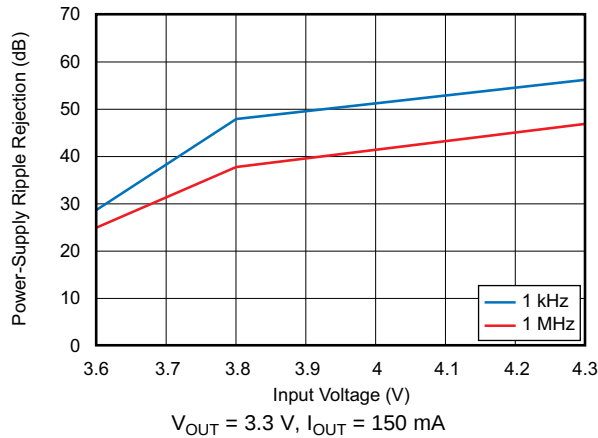


图 27. Power-Supply Ripple Rejection vs Input Voltage

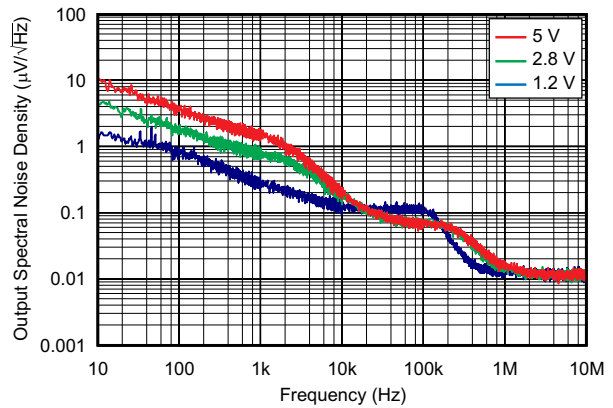


图 28. Output Spectral Noise Density vs Frequency

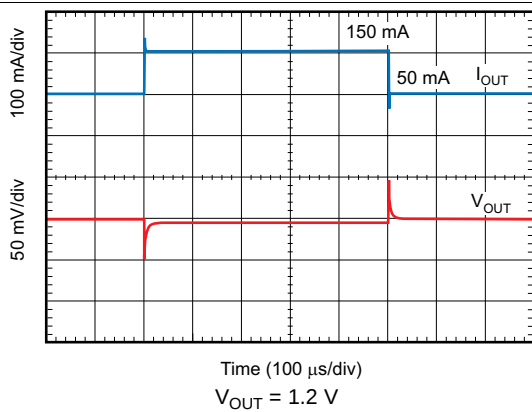


图 29. Load Transient Response

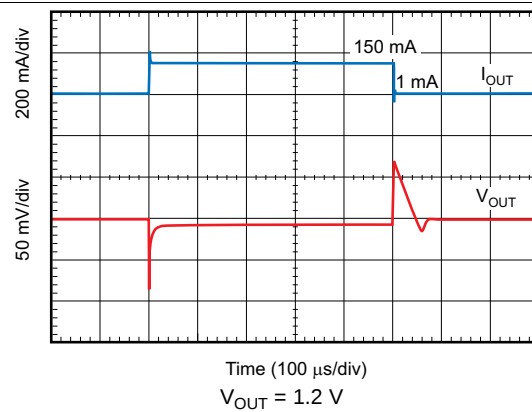


图 30. Load Transient Response

Typical Characteristics (接下页)

at $T_J = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ or 2 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, and $C_{OUT} = 1\text{ }\mu\text{F}$
Typical values are at $T_J = 25^{\circ}\text{C}$, (unless otherwise noted)

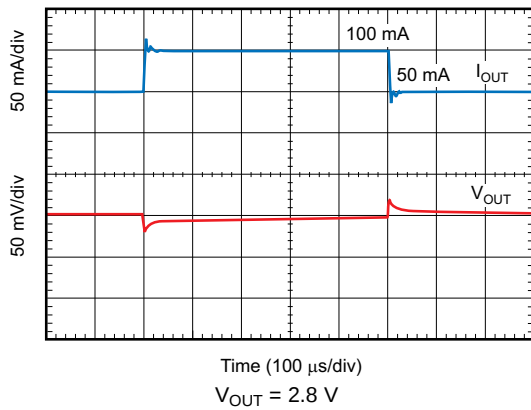


图 31. Load Transient Response

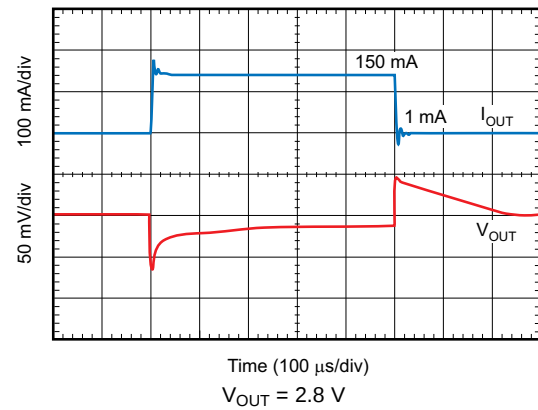


图 32. Load Transient Response

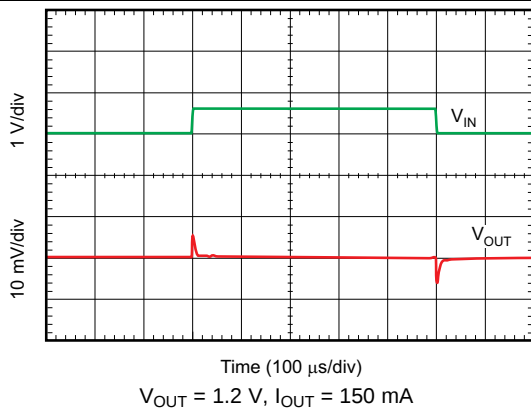


图 33. Line Transient Response

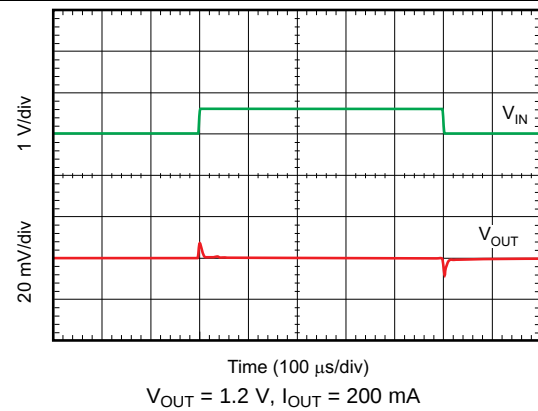


图 34. Line Transient Response

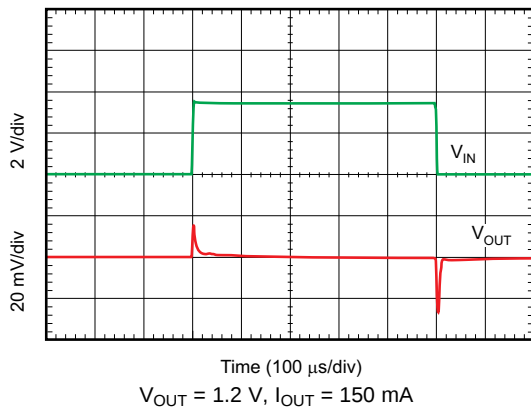


图 35. Line Transient Response

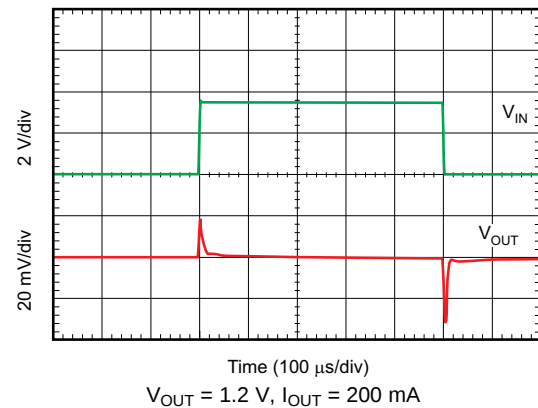


图 36. Line Transient Response

Typical Characteristics (接下页)

at $T_J = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{IN} = V_{OUT(NOM)} + 0.5\text{ V}$ or 2 V (whichever is greater), $I_{OUT} = 10\text{ mA}$, $V_{EN} = V_{IN}$, and $C_{OUT} = 1\text{ }\mu\text{F}$
 Typical values are at $T_J = 25^{\circ}\text{C}$, (unless otherwise noted)

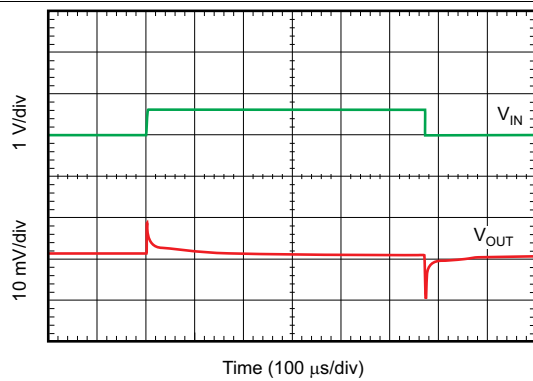


图 37. Line Transient Response

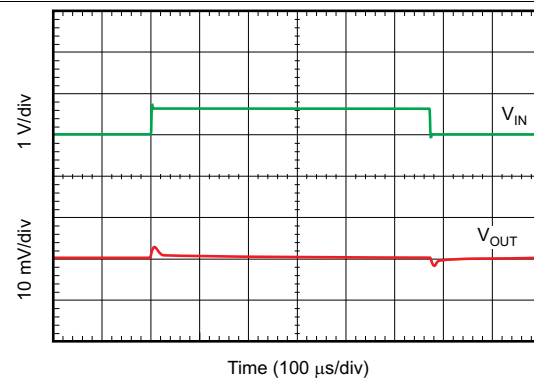


图 38. Line Transient Response

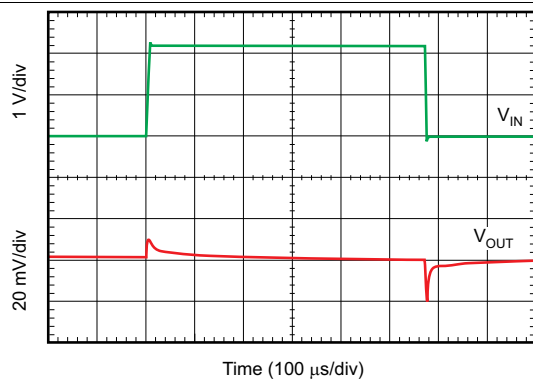


图 39. Line Transient Response

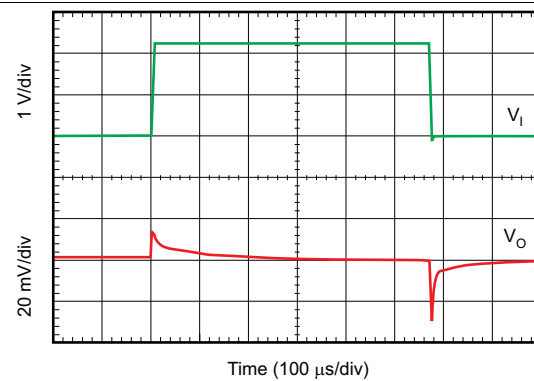


图 40. Line Transient Response

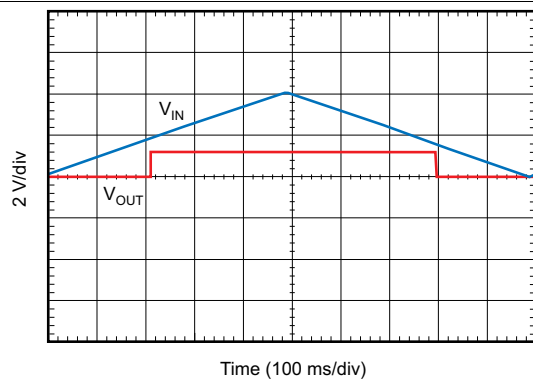


图 41. V_{IN} Ramp Up, Ramp Down Response

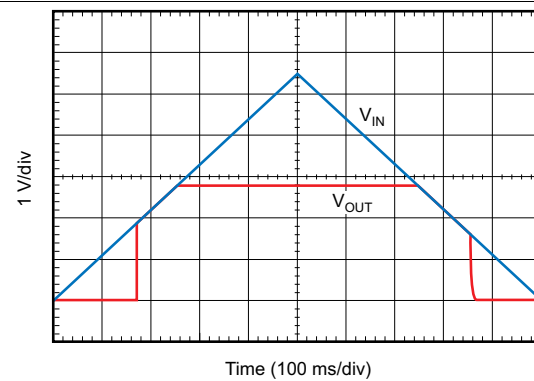


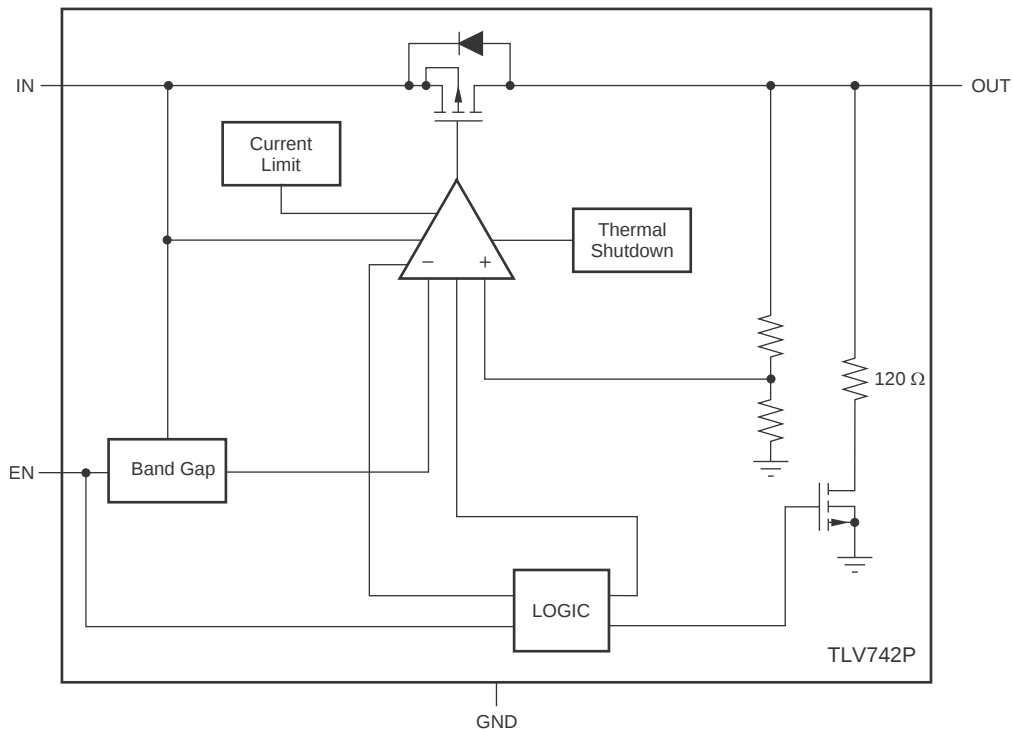
图 42. V_{IN} Ramp Up, Ramp Down Response

7 Detailed Description

7.1 Overview

The TLV742P device belongs to a family of LDOs. This device consumes low quiescent current and delivers excellent line and load transient performance. These characteristics [combined with low noise and very good PSRR with little ($V_{IN} - V_{OUT}$) headroom] make this device ideal for portable RF applications.

7.2 Functional Block Diagrams



Copyright © 2017, Texas Instruments Incorporated

图 43. TLV742P Block Diagram

7.3 Feature Description

This LDO regulator offers current limit and thermal protection. The operating junction temperature of this device is -40°C to $+125^{\circ}\text{C}$.

7.3.1 Internal Current Limit

The internal current limit helps to protect the regulator during fault conditions. During current limit, the output sources a fixed amount of current that is largely independent of the output voltage. In such a case, the output voltage is not regulated, and is $V_{OUT} = I_{CL} \times R_L$. The PMOS pass transistor dissipates $(V_{IN} - V_{OUT}) \times I_{LIMIT}$ until thermal shutdown is triggered and the device turns off. When the device cools, the internal thermal shutdown circuit turns the device back on. If the fault condition continues, the device cycles between current limit and thermal shutdown; see [Thermal Information](#) for more details.

The PMOS pass element has a built-in body diode that conducts current when the voltage at OUT exceeds the voltage at IN. This current is not limited, so if extended reverse voltage operation is anticipated, external limiting to 5% of the rated output current is recommended.

Feature Description (接下页)

7.3.2 Shutdown

The enable pin (EN) is active high. The device is enabled when voltage at the EN pin goes above 0.9 V. The device is turned off when the EN pin is held at less than 0.4 V. When shutdown capability is not required, EN can be connected to the IN pin.

The TLV742P version has internal active pulldown circuitry that discharges the output with a time constant as given by [公式 1](#):

$$\tau = \frac{(120 \cdot R_L)}{(120 + R_L)} \cdot C_{OUT}$$

where:

- R_L = Load resistance
- C_{OUT} = Output capacitor

(1)

7.4 Device Functional Modes

The TLV742P series is specified over the recommended operating conditions (see [Recommended Operating Conditions](#)). The specifications may not be met when exposed to conditions outside of the recommended operating range.

To turn on the regulator, the EN pin must be driven over 0.9 V. Driving the EN pin below 0.4 V causes the regulator to enter shutdown mode.

In shutdown, the current consumption of the device typically reduces to 1 μ A.

8 Application and Implementation

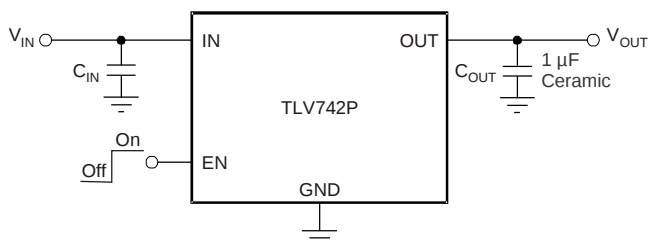
注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TLV742P is a LDO with low quiescent current that delivers excellent line and load transient performance. This LDO regulator offers current limit and thermal protection. The operating junction temperature of this device series is -40°C to $+125^{\circ}\text{C}$.

8.2 Typical Application



Copyright © 2017, Texas Instruments Incorporated

图 44. Typical Application Circuit

8.2.1 Design Requirements

Provide an input supply with adequate headroom to meet minimum V_{IN} requirements (as listed in [表 1](#)), compensate for the GND pin current, and to power the load.

表 1. Design Parameters

PARAMETER	DESIGN REQUIREMENT
Input voltage	1.8 V to 3.6 V
Output voltage	1.2 V
Output current	100 mA

8.2.2 Detailed Design Procedure

8.2.2.1 Input and Output Capacitor Requirements

Generally, 1- μ F X5R- and X7R-type ceramic capacitors are recommended because these capacitors have minimal variation in value and equivalent series resistance (ESR) over temperature.

However, the TLV742P is designed to be stable with an effective capacitance of 0.1 μ F or larger at the output. As a result, the device is stable with capacitors of other dielectric types if the effective capacitance under operating bias voltage and temperature is greater than 0.1 μ F. This effective capacitance refers to the capacitance that the LDO detects under operating bias voltage and temperature conditions; that is, the capacitance after taking bias voltage and temperature derating into consideration. In addition to using less expensive dielectrics, this stability with 0.1- μ F effective capacitance enables the use of smaller footprint capacitors that have higher derating in size- and space-constrained applications.

Using a 0.1- μ F rated capacitor at the output of the LDO does not ensure stability because the effective capacitance under the specified operating conditions is less than 0.1 μ F. Maximum ESR must be less than 200 m Ω .

Although an input capacitor is not required for stability, good analog design practice is to connect a 0.1- μ F to 1- μ F, low ESR capacitor across the IN pin and GND pin of the regulator. This capacitor counteracts reactive input sources and improves transient response, noise rejection, and ripple rejection. A higher-value capacitor may be required if large, fast rise-time load transients are anticipated, or if the device is not located close to the power source. If source impedance is more than 2- Ω , a 0.1- μ F input capacitor may be required to ensure stability.

8.2.2.2 Dropout Voltage

The TLV742P series of LDOs use a PMOS pass transistor to achieve low dropout. When ($V_{IN} - V_{OUT}$) is less than the dropout voltage (V_{DO}), the PMOS pass device is in the linear region of operation and the input-to-output resistance is the $R_{DS(ON)}$ of the PMOS pass element. V_{DO} scales approximately with output current because the PMOS device functions similar to a resistor in dropout.

PSRR and transient response degrade when ($V_{IN} - V_{OUT}$) approaches dropout.

8.2.2.3 Transient Response

Increasing the size of the output capacitor reduces overshoot and undershoot magnitude but increases the duration of the transient response.

8.2.3 Application Curves

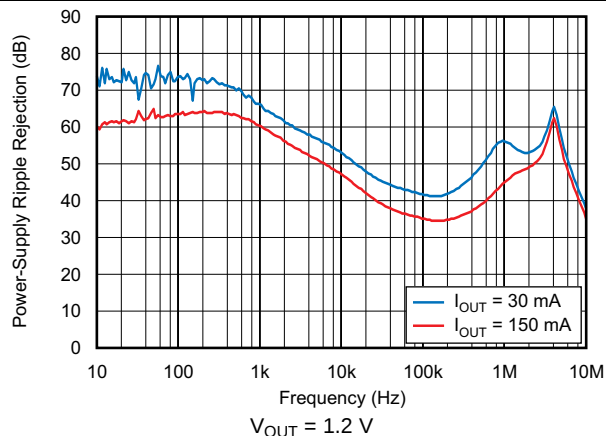


图 45. Power-Supply Ripple Rejection vs Frequency

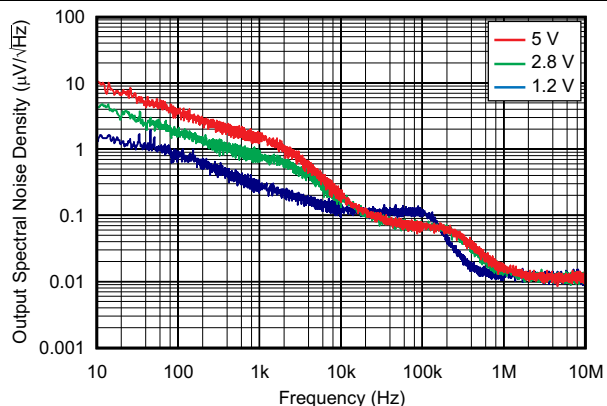


图 46. Output Spectral Noise Density vs Frequency

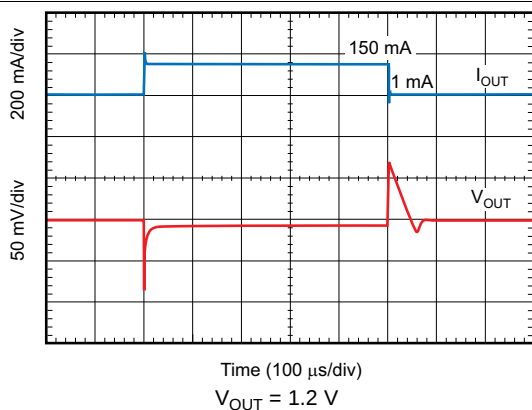


图 47. Load Transient Response

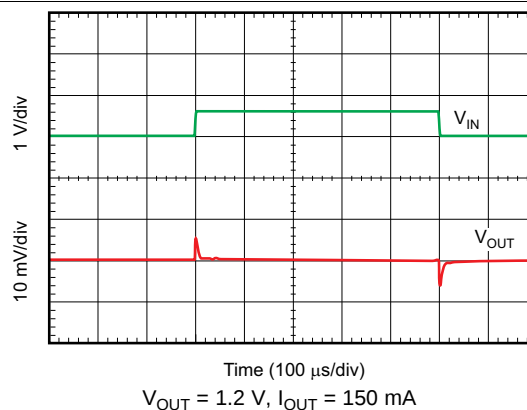


图 48. Line Transient Response

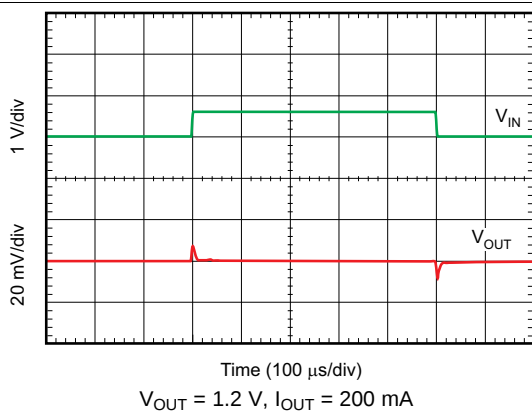


图 49. Line Transient Response

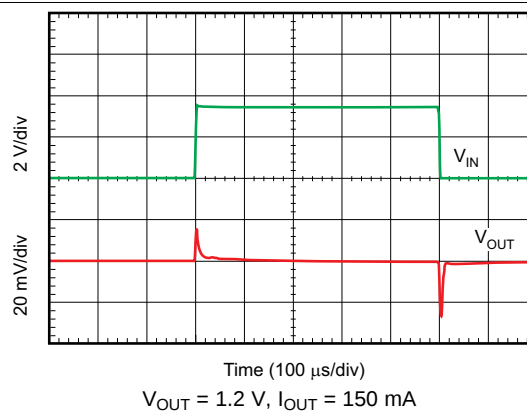


图 50. Line Transient Response

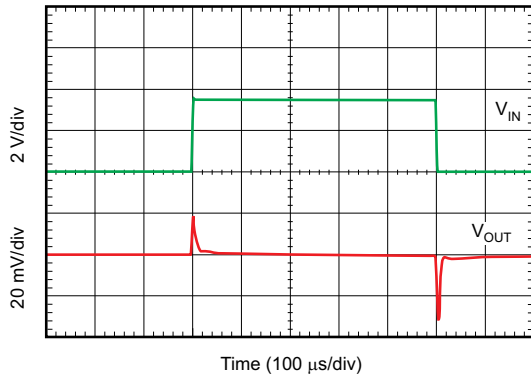
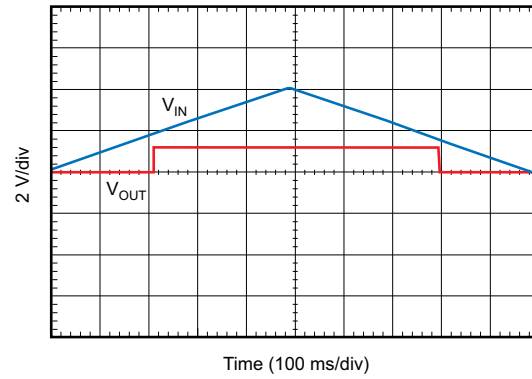


图 51. Line Transient Response


 图 52. V_{IN} Ramp Up, Ramp Down Response

8.3 Do's and Don'ts

Place at least one 1- μ F ceramic capacitor as close as possible to the OUT pin of the regulator.

Do not place the output capacitor more than 10 mm away from the regulator.

Connect a 1- μ F low equivalent series resistance (ESR) capacitor across the IN pin and GND input of the regulator for improved transient performance.

Do not exceed the absolute maximum ratings.

9 Power Supply Recommendations

The device is designed to operate from an input voltage supply range between 2 V and 5.5 V. The input voltage range provides adequate headroom for the device to have a regulated output. This input supply must be well-regulated (see 图 33 through 图 40). If the input supply is noisy, additional input capacitors with low ESR help improve the output noise performance.

10 Layout

10.1 Layout Guidelines

10.1.1 Board Layout Recommendations to Improve PSRR and Noise Performance

Place input and output capacitors as close to the device pins as possible. To improve ac performance (such as PSRR, output noise, and transient response), TI recommends that the board be designed with separate ground planes for V_{IN} and V_{OUT} , with the ground plane connected only at the GND pin of the device, as shown in 图 53. Connect the ground connection for the output capacitor directly to the GND pin of the device. High ESR capacitors can degrade PSRR performance.

10.1.2 Package Mounting

Solder pad footprint recommendations are available from the TI website at www.ti.com. The recommended land pattern for the DQN (X2SON-4) package is provided in the 机械、封装和可订购信息 section.

10.2 Layout Example

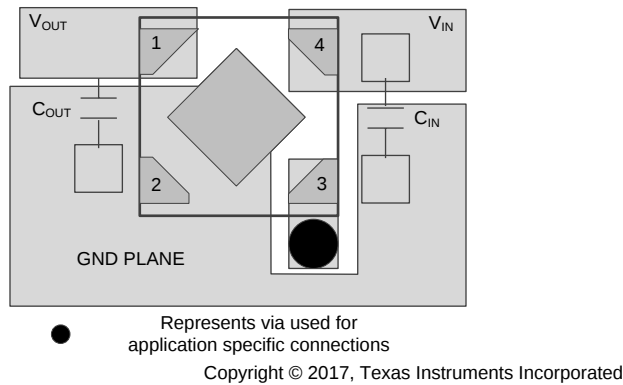


图 53. Recommended Layout Example

10.3 Thermal Considerations

Thermal protection disables the output when the junction temperature rises to approximately 160°C, allowing the device to cool. When the junction temperature cools to approximately 140°C, the output circuitry is enabled again. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits the dissipation of the regulator, which protects the regulator from damage as a result of overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heat sink. For reliable operation, limit junction temperature to 125°C (maximum). To estimate the margin of safety in a complete design (including heat sink), increase the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions.

For good reliability, thermal protection triggers at least 35°C above the maximum expected ambient condition of the particular application. This configuration produces a worst-case junction temperature of 125°C at the highest expected ambient temperature and worst-case load.

The internal protection circuitry of the LDO is designed to protect against overload conditions. This circuitry is not intended to replace proper heat sinking. Continuously running the LDO into thermal shutdown degrades device reliability.

10.4 Power Dissipation

The ability to remove heat from the die is different for each package type, presenting different considerations in the printed-circuit-board (PCB) layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air.

Performance data for JEDEC low- and high-K boards are shown in [Thermal Information](#). Using heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers improves heat sink effectiveness.

Power dissipation depends on input voltage and load conditions. Power dissipation (P_D) is equal to the product of the output current and the voltage drop across the output pass element, as shown in [公式 2](#).

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (2)$$

11 器件和文档支持

11.1 器件支持

11.1.1 开发支持

11.1.1.1 评估模块

我们提供了一款评估模块 (EVM)，可与 TLV742P 配套使用，帮助评估初始电路性能。 [TLV70728EVM-612](#) 详细介绍了 TLV70728EVM-612 的设计套件和评估模块。

可通过德州仪器 (TI) 网站上的 [TLV742P](#) 产品文件夹申请获取该 EVM，也可以直接从 [TI 网上商店](#) 购买。

11.1.2 器件命名规则

订购信息 ⁽¹⁾

产品	V _{OUT} ⁽²⁾
TLV742xx(x)Pyyyz	XX(X) 是标称输出电压。对于分辨率为 100mV 的输出电压，订货编号中使用两位数字；否则，使用三位数字（例如，18 = 1.8V，285 = 2.85V）。 P 为可选项；P 表示器件具有一个带有源输出放电功能的 LDO 稳压器。 YYY 为封装标识符。 Z 为封装数量。 R 表示卷（3000 片）， T 表示带（250 片）。

(1) 要获得最新的封装和订货信息，请参阅本文档末尾的封装选项附录，或者访问器件产品文件夹，此文件夹位于 [www.ti.com.cn](#) 内。

(2) 可提供 0.85V 至 5V 范围内的输出电压（以 50mV 为单位增量）。请与厂方联系以了解详细信息和可用性。

11.2 接收文档更新通知

要接收文档更新通知，请导航至 [TI.com](#) 上的器件产品文件夹。单击右上角的 [通知我](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [《使用条款》](#)。

TI E2E™ 在线社区 [TI 的工程师对工程师 \(E2E\) 社区](#)。此社区的创建目的在于促进工程师之间的协作。在 [e2e.ti.com](#) 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 [TI 参考设计支持](#) 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

11.4 商标

E2E is a trademark of Texas Instruments.

11.5 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会导致损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。这些数据如有变更，恕不另行通知和修订此文档。如欲获取此产品说明书的浏览器版本，请参阅左侧的导航。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TLV74211PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8H
TLV74211PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8H
TLV74212PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8G
TLV74212PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8G
TLV74215PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8F
TLV74215PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8F
TLV74218PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8E
TLV74218PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8E
TLV74218PDQNRG4.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8E
TLV74225PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CS
TLV74225PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CS
TLV74227PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8D
TLV74227PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8D
TLV74228PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8C
TLV74228PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8C
TLV74229PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8B
TLV74229PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	8B
TLV74230PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CT
TLV74230PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CT
TLV74230PDQNRG4.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CT
TLV74233PDQNR	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	7Z
TLV74233PDQNR.B	Active	Production	X2SON (DQN) 4	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	7Z

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV74211PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74212PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74215PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74218PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74225PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74227PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74228PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74229PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74230PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
TLV74233PDQNR	X2SON	DQN	4	3000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV74211PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74212PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74215PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74218PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74225PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74227PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74228PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74229PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74230PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0
TLV74233PDQNR	X2SON	DQN	4	3000	210.0	185.0	35.0

DQN 4

GENERIC PACKAGE VIEW

X2SON - 0.4 mm max height

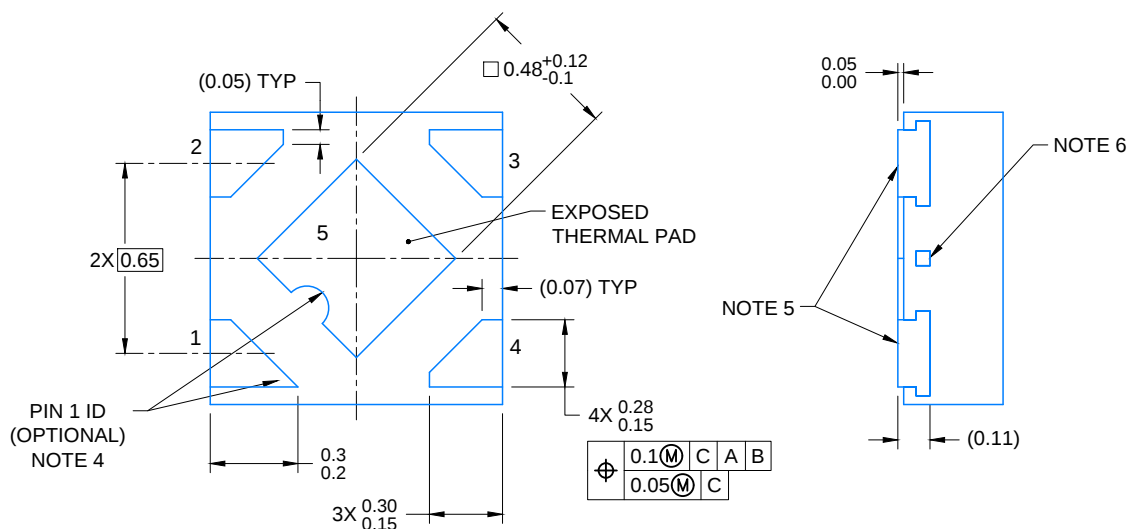
PLASTIC SMALL OUTLINE - NO LEAD



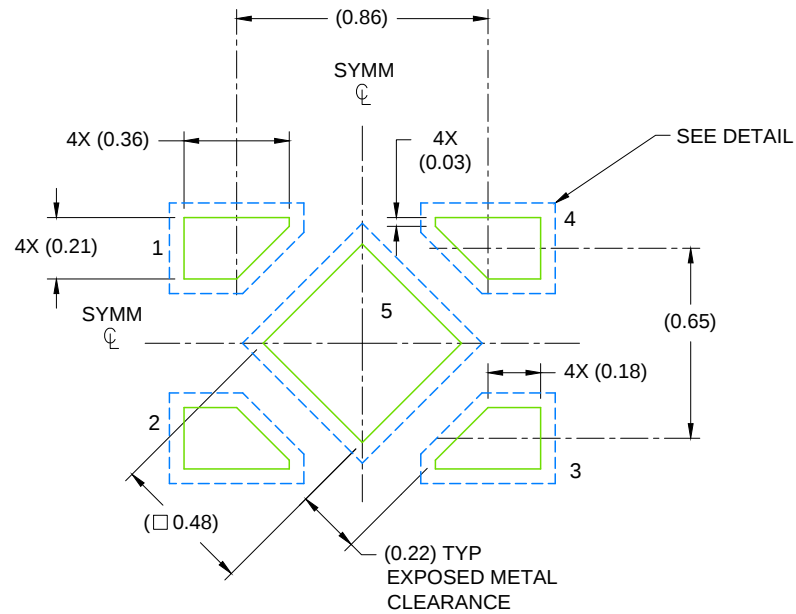
Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4210367/F

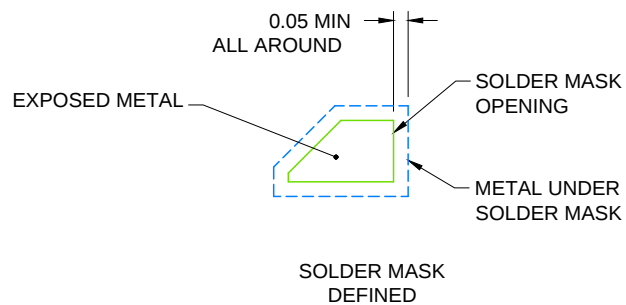
PLASTIC SMALL OUTLINE - NO LEAD



**TEXAS
INSTRUMENTS**
www.ti.com



LAND PATTERN EXAMPLE
SCALE: 40X

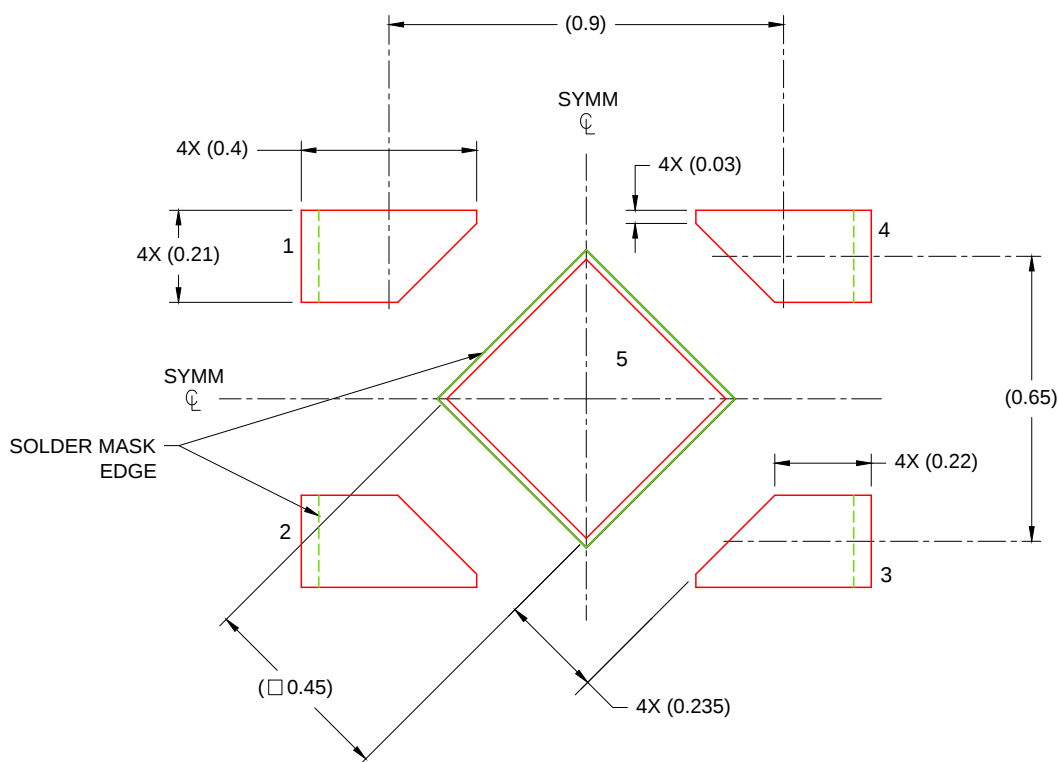


SOLDER MASK DETAIL

4215302/E 12/2016

NOTES: (continued)

7. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
8. If any vias are implemented, it is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
 BASED ON 0.075 - 0.1mm THICK STENCIL

EXPOSED PAD
 88% PRINTED SOLDER COVERAGE BY AREA
 SCALE: 60X

4215302/E 12/2016

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要通知和免责声明

TI“按原样”提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的相关应用。严禁以其他方式对这些资源进行复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 [TI 的销售条款](#) 或 [ti.com](#) 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
版权所有 © 2025，德州仪器 (TI) 公司